Product data sheet

1. General description

Hyperfast power diode in a 2-lead TO220 plastic package.





2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- · Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; $T_{mb} \le 127$ °C; Fig. 1; Fig. 2; Fig. 3			8		Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 127 °C; square-wave pulse			16		Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		91		Α	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse					Α
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.20	3.20	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.45	2.45	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	13	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	5 0 7	1/ 1/1 A
2	Α	anode	Ţ ŲŢ	K A 001aaa020
mb	mb	mounting base; connected to cathod		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC8M-650P	TO220-2L	BYC8M-650PQ	Tube	50	TO220d-2L	13-Oct-2022

7. Marking

Table 4. Marking codes

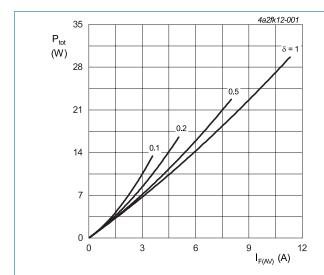
Type number	Marking codes
BYC8M-650P	BYC8M 650P

8. Limiting values

Table 5. Limiting values

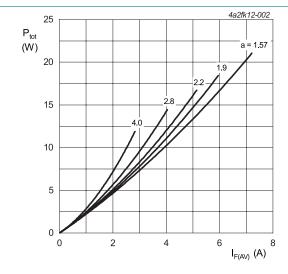
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 127$ °C; Fig. 1; Fig. 2; Fig. 3		8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 127 °C; square-wave pulse		16	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		100	Α
T _{stg}	storage temperature			-65 to 175	°C
T _j	junction temperature			-65 to 175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 2.097 \text{ V; } R_s = 0.0464 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 2.097 V; R_s = 0.0464 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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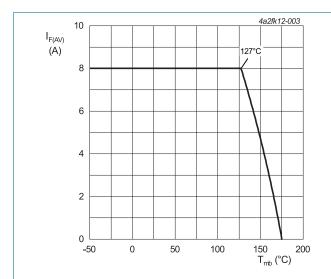


Fig. 3. Forward current as a function of mounting base temperature; maximum values

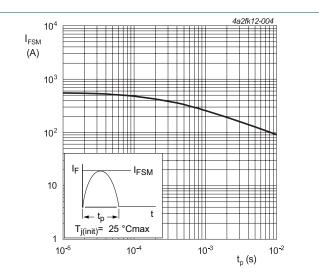


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	-	2.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

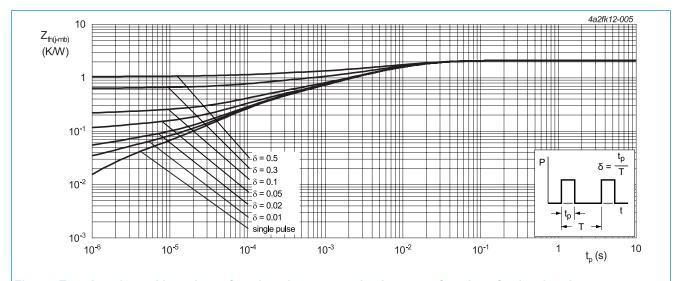
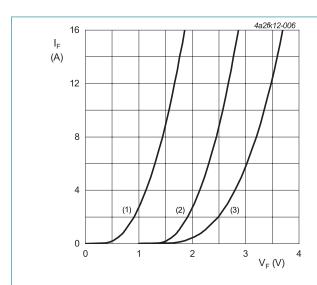


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics			,			
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.20	3.20	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.45	2.45	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.6	30	μΑ
		V _R = 650 V; T _j = 150 °C		-	0.07	0.8	mA
Dynamic	characteristics						
Q _r	reverse charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	38	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	93	-	nC
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	20	-	ns
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	13	-	ns
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	28	-	ns
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	45	-	ns
I _{RM}	peak reverse recovery currentnon-repetitive avalanche energy	$I_F = 8 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	2.7	-	А
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	4.2	-	А
E _{as}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		10.8	-	-	mJ



 $V_0 = 2.097 \text{ V}; R_s = 0.0464 \Omega$

(1) T_i = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values



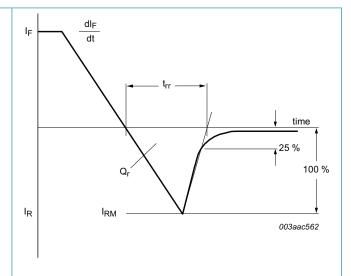


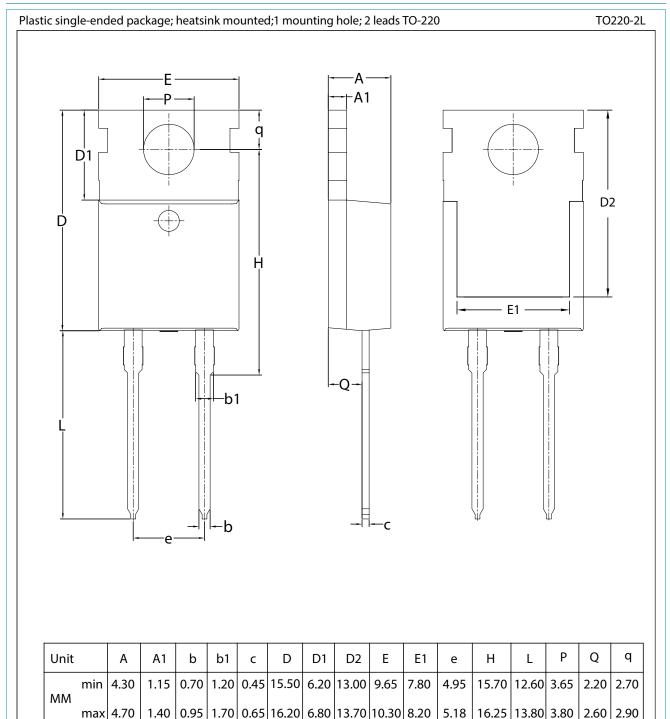
Fig. 7. Reverse recovery definitions; ramp recovery

BYC8M-650P

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11. Package outline



Note:

max 4.70

1.40

All dimensions don't include mold flash and metal protrusion.

0.95 | 1.70 | 0.65 | 16.20 |

16.25 | 13.80 | 3.80 | 2.60 | 2.90

5.18

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10	. Characteristics	6
11	. Package outline	7
12	. Legal information	8
	. Contents	

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